

CPC COOPERATIVE PATENT CLASSIFICATION

H ELECTRICITY

(NOTE omitted)

H03 ELECTRONIC CIRCUITRY

H03B GENERATION OF OSCILLATIONS, DIRECTLY OR BY FREQUENCY-CHANGING, BY CIRCUITS EMPLOYING ACTIVE ELEMENTS WHICH OPERATE IN A NON-SWITCHING MANNER; GENERATION OF NOISE BY SUCH CIRCUITS ([generators adapted for electrophonic musical instruments G10H](#); [masers or lasers H01S](#); [generation of oscillations in plasma H05H](#))

WARNING

In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

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|-------------|---|--------|---|
| 1/00 | Details | 5/1231 | . . . {the amplifier comprising one or more bipolar transistors} |
| 1/02 | . Structural details of power oscillators, e.g. for heating (construction of transmitters H04B ; features of generators for heating by electromagnetic fields H05B 6/00) | 5/1234 | . . . {and comprising means for varying the output amplitude of the generator (H03B 5/1278 takes precedence)} |
| 1/04 | . Reducing undesired oscillations, e.g. harmonics | 5/1237 | . . . {comprising means for varying the frequency of the generator} |
| 5/00 | Generation of oscillations using amplifier with regenerative feedback from output to input (H03B 9/00, H03B 15/00 take precedence) | 5/124 | {the means comprising a voltage dependent capacitance} |
| 5/02 | . Details | 5/1243 | {the means comprising voltage variable capacitance diodes} |
| 5/04 | . . Modifications of generator to compensate for variations in physical values, e.g. power supply, load, temperature | 5/1246 | {the means comprising transistors used to provide a variable capacitance} |
| 5/06 | . . Modifications of generator to ensure starting of oscillations | 5/125 | {the transistors being bipolar transistors} |
| 5/08 | . with frequency-determining element comprising lumped inductance and capacitance | 5/1253 | {the transistors being field-effect transistors} |
| 5/10 | . . active element in amplifier being vacuum tube (H03B 5/14 takes precedence) | 5/1256 | {the means comprising a variable inductance} |
| 5/12 | . . active element in amplifier being semiconductor device (H03B 5/14 takes precedence) | 5/1259 | {the means comprising a variable active inductor, e.g. gyrator circuits} |
| 5/1203 | . . . {the amplifier being a single transistor} | 5/1262 | {the means comprising switched elements} |
| 5/1206 | . . . {using multiple transistors for amplification} | 5/1265 | {switched capacitors} |
| 5/1209 | {the amplifier having two current paths operating in a differential manner and a current source or degeneration circuit in common to both paths, e.g. a long-tailed pair. (H03B 5/1215 takes precedence)} | 5/1268 | {switched inductors} |
| 5/1212 | {the amplifier comprising a pair of transistors, wherein an output terminal of each being connected to an input terminal of the other, e.g. a cross coupled pair} | 5/1271 | {the frequency being controlled by a control current, i.e. current controlled oscillators} |
| 5/1215 | {the current source or degeneration circuit being in common to both transistors of the pair, e.g. a cross-coupled long-tailed pair} | 5/1275 | {having further means for varying a parameter in dependence on the frequency} |
| 5/1218 | {the generator being of the balanced type} | 5/1278 | {the parameter being an amplitude of a signal, e.g. maintaining a constant output amplitude over the frequency range} |
| 5/1221 | {the amplifier comprising multiple amplification stages connected in cascade} | 5/1281 | {the parameter being the amount of feedback} |
| 5/1225 | {the generator comprising multiple amplifiers connected in parallel} | 5/1284 | {the parameter being another frequency, e.g. a harmonic of the oscillating frequency} |
| 5/1228 | . . . {the amplifier comprising one or more field effect transistors} | 5/1287 | {the parameter being a quality factor, e.g. Q factor of the frequency determining element} |
| | | 5/129 | {the parameter being a bias voltage or a power supply} |

- 5/1293 . . . {having means for achieving a desired tuning characteristic, e.g. linearising the frequency characteristic across the tuning voltage range}
- 5/1296 . . . {the feedback circuit comprising a transformer}
- 5/14 . . frequency-determining element connected via bridge circuit to closed ring around which signal is transmitted
- 5/16 . . . active element in amplifier being vacuum tube
- 5/18 . with frequency-determining element comprising distributed inductance and capacitance
- 5/1805 . . {the frequency-determining element being a coaxial resonator}
- 5/1811 . . . {the active element in the amplifier being a vacuum tube (see provisionally also H03B 5/1835)}
- 5/1817 . . {the frequency-determining element being a cavity resonator}
- 5/1823 . . . {the active element in the amplifier being a semiconductor device}
- 5/1829 {the semiconductor device being a field-effect device}
- 5/1835 . . . {the active element in the amplifier being a vacuum tube}
- 5/1841 . . {the frequency-determining element being a strip line resonator (H03B 5/1805, H03B 5/1817, H03B 5/1864 and H03B 5/1882 take precedence)}
- 5/1847 . . . {the active element in the amplifier being a semiconductor device}
- 5/1852 {the semiconductor device being a field-effect device}
- 5/1858 . . . {the active element in the amplifier being a vacuum tube (see provisionally also H03B 5/1835)}
- 5/1864 . . {the frequency-determining element being a dielectric resonator}
- 5/187 . . . {the active element in the amplifier being a semiconductor device}
- 5/1876 {the semiconductor device being a field-effect device}
- 5/1882 . . {the frequency-determining element being a magnetic-field sensitive resonator, e.g. a Yttrium Iron Garnet or a magnetostatic surface wave resonator}
- 5/1888 . . . {the active element in the amplifier being a semiconductor device}
- 5/1894 {the semiconductor device being a field-effect device}
- 5/20 . with frequency-determining element comprising resistance and either capacitance or inductance, e.g. phase-shift oscillator
- 5/22 . . active element in amplifier being vacuum tube (H03B 5/26 takes precedence)
- 5/24 . . active element in amplifier being semiconductor device (H03B 5/26 takes precedence)
- 5/26 . . frequency-determining element being part of bridge circuit in closed ring around which signal is transmitted; frequency-determining element being connected via a bridge circuit to such a closed ring, e.g. Wien-Bridge oscillator, parallel-T oscillator
- 5/28 . . . active element in amplifier being vacuum tube
- 5/30 . with frequency-determining element being electromechanical resonator
- 5/32 . . being a piezoelectric resonator (selection of piezoelectric material H10N 30/00)
- 5/323 . . . {the resonator having more than two terminals (H03B 5/326 takes precedence)}
- 5/326 . . . {the resonator being an acoustic wave device, e.g. SAW or BAW device}
- 5/34 . . . active element in amplifier being vacuum tube (H03B 5/38 takes precedence)
- 5/36 . . . active element in amplifier being semiconductor device ((H03B 5/323, H03B 5/326), H03B 5/38 take precedence)
- 5/362 {the amplifier being a single transistor (H03B 5/364 - H03B 5/368 take precedence)}
- 5/364 {the amplifier comprising field effect transistors (H03B 5/366 takes precedence)}
- 5/366 {and comprising means for varying the frequency by a variable voltage or current}
- 5/368 {the means being voltage variable capacitance diodes}
- 5/38 . . . frequency-determining element being connected via bridge circuit to closed ring around which signal is transmitted
- 5/40 . . being a magnetostrictive resonator (H03B 5/42 takes precedence; selection of magneto-strictive material {H01F 1/00}; H10N 30/00)
- 5/42 . . frequency-determining element connected via bridge circuit to closed ring around which signal is transmitted
- 7/00 Generation of oscillations using active element having a negative resistance between two of its electrodes (H03B 9/00 takes precedence)**
- 7/02 . with frequency-determining element comprising lumped inductance and capacitance
- 7/04 . . active element being vacuum tube
- 7/06 . . active element being semiconductor device
- 7/08 . . . being a tunnel diode
- 7/10 . . active element being gas-discharge or arc-discharge tube
- 7/12 . with frequency-determining element comprising distributed inductance and capacitance
- 7/14 . . active element being semiconductor device
- 7/143 . . . {and which comprises an element depending on a voltage or a magnetic field, e.g. varactor-YIG}
- 7/146 . . . {with several semiconductor devices}
- 9/00 Generation of oscillations using transit-time effects {(construction of tube and circuit arrangements not adapted to a particular application H01L; construction of the semiconductor devices H01L)}**
- 9/01 . using discharge tubes
- 9/02 . . using a retarding-field tube (using klystrons H03B 9/04)
- 9/04 . . using a klystron
- 9/06 . . . using a reflex klystron
- 9/08 . . using a travelling-wave tube
- 9/10 . . using a magnetron
- 9/12 . using solid state devices, e.g. Gunn-effect devices
- 2009/123 . . {using Gunn diodes}
- 2009/126 . . {using impact ionization avalanche transit time [IMPATT] diodes}

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|--------------|--|----------------|---|
| 9/14 | . . and elements comprising distributed inductance and capacitance | 21/01 | . by beating unmodulated signals of different frequencies |
| 9/141 | . . . {and comprising a voltage sensitive element, e.g. varactor} | 21/02 | . . by plural beating, i.e. for frequency synthesis {; Beating in combination with multiplication or division of frequency (digital frequency synthesis using a ROM G06F 1/02; digital frequency synthesis in general H03K; indirect frequency synthesis using a PLL H03L 7/16)} |
| 9/142 | . . . {and comprising a magnetic field sensitive element, e.g. YIG} | 21/025 | . . . {by repeated mixing in combination with division of frequency only} |
| 9/143 | . . . {using more than one solid state device} | 21/04 | . . using several similar stages |
| 9/145 | . . . {the frequency being determined by a cavity resonator, e.g. a hollow waveguide cavity or a coaxial cavity (H03B 9/141 - H03B 9/143, H03B 9/147, H03B 9/148 take precedence)} | 23/00 | Generation of oscillations periodically swept over a predetermined frequency range (angle-modulating circuits in general H03C 3/00) |
| 9/146 | {formed by a disc, e.g. a waveguide cap resonator} | 25/00 | Simultaneous generation by a free-running oscillator of oscillations having different frequencies |
| 9/147 | . . . {the frequency being determined by a stripline resonator (H03B 9/141 - H03B 9/143, H03B 9/148 take precedence)} | 27/00 | Generation of oscillations providing a plurality of outputs of the same frequency but differing in phase, other than merely two anti-phase outputs |
| 9/148 | . . . {the frequency being determined by a dielectric resonator (H03B 9/141 - H03B 9/143 take precedence)} | 28/00 | Generation of oscillations by methods not covered by groups H03B 5/00 - H03B 27/00, including modification of the waveform to produce sinusoidal oscillations (analogue function generators for performing computing operations G06G 7/26; use of transformers for conversion of waveform in AC-AC converters H02M 5/18) |
| 11/00 | Generation of oscillations using a shock-excited tuned circuit (with feedback H03B 5/00) | 29/00 | Generation of noise currents and voltages {(gasfilled discharge tubes with solid cathode specially adapted as noise generators H01J 17/005)} |
| 11/02 | . excited by spark (spark gaps therefor H01T 9/00) | 2200/00 | Indexing scheme relating to details of oscillators covered by H03B |
| 11/04 | . excited by interrupter | 2200/0002 | . Types of oscillators |
| 11/06 | . . by mechanical interrupter | 2200/0004 | . . Butler oscillator |
| 11/08 | . . interrupter being discharge tube | 2200/0006 | . . Clapp oscillator |
| 11/10 | . . interrupter being semiconductor device | 2200/0008 | . . Colpitts oscillator |
| 13/00 | Generation of oscillations using deflection of electron beam in a cathode-ray tube | 2200/001 | . . Hartley oscillator |
| 15/00 | Generation of oscillations using galvano-magnetic devices, e.g. Hall-effect devices, or using superconductivity effects | 2200/0012 | . . Pierce oscillator |
| 15/003 | . {using superconductivity effects (devices using superconductivity H10N 60/00)} | 2200/0014 | . Structural aspects of oscillators |
| 15/006 | . {using spin transfer effects or giant magnetoresistance} | 2200/0016 | . . including a ring, disk or loop shaped resonator |
| 17/00 | Generation of oscillations using radiation source and detector, e.g. with interposed variable obturator | 2200/0018 | . . relating to the cutting angle of a crystal, e.g. AT cut quartz |
| 19/00 | Generation of oscillations by non-regenerative frequency multiplication or division of a signal from a separate source (transference of modulation from one carrier to another H03D 7/00) | 2200/002 | . . making use of ceramic material |
| 19/03 | . using non-linear inductance | 2200/0022 | . . characterised by the substrate, e.g. material |
| 19/05 | . using non-linear capacitance, e.g. varactor diodes | 2200/0024 | . . including parallel striplines |
| 19/06 | . by means of discharge device or semiconductor device with more than two electrodes | 2200/0026 | . . relating to the pins of integrated circuits |
| 19/08 | . . by means of a discharge device | 2200/0028 | . . based on a monolithic microwave integrated circuit [MMIC] |
| 19/10 | . . . using multiplication only | 2200/003 | . Circuit elements of oscillators |
| 19/12 | . . . using division only | 2200/0032 | . . including a device with a Schottky junction |
| 19/14 | . . by means of a semiconductor device | 2200/0034 | . . including a buffer amplifier |
| 19/16 | . using uncontrolled rectifying devices, e.g. rectifying diodes or Schottky diodes | 2200/0036 | . . including an emitter or source coupled transistor pair or a long tail pair |
| 19/18 | . . and elements comprising distributed inductance and capacitance | 2200/0038 | . . including a current mirror |
| 19/20 | . . being diodes exhibiting charge storage or enhancement effects | 2200/004 | . . including a variable capacitance, e.g. a varicap, a varactor or a variable capacitance of a diode or transistor |
| 21/00 | Generation of oscillations by combining unmodulated signals of different frequencies (H03B 19/00 takes precedence; frequency changing circuits in general H03D) | 2200/0042 | . . . the capacitance diode being in the feedback path |

- 2200/0044 . . including optical elements, e.g. optical injection locking
- 2200/0046 . . including measures to switch the gain of an amplifier
- 2200/0048 . . including measures to switch the frequency band, e.g. by harmonic selection
- 2200/005 . . including measures to switch a capacitor
- 2200/0052 . . including measures to switch the feedback circuit
- 2200/0054 . . including measures to switch a filter, e.g. for frequency tuning or for harmonic selection
- 2200/0056 . . including a diode used for switching
- 2200/0058 . . with particular transconductance characteristics, e.g. an operational transconductance amplifier
- 2200/006 . Functional aspects of oscillators
- 2200/0062 . . Bias and operating point
- 2200/0064 . . Pulse width, duty cycle or on/off ratio
- 2200/0066 . . Amplitude or AM detection
- 2200/0068 . . Frequency or FM detection
- 2200/007 . . Generation of oscillations based on harmonic frequencies, e.g. overtone oscillators
- 2200/0072 . . Frequency hopping and enabling of rapid frequency changes
- 2200/0074 . . Locking of an oscillator by injecting an input signal directly into the oscillator
- 2200/0076 . . Power combination of several oscillators oscillating at the same frequency
- 2200/0078 . . generating or using signals in quadrature
- 2200/008 . . making use of a reference frequency
- 2200/0082 . . Lowering the supply voltage and saving power
- 2200/0084 . . dedicated to Terahertz frequencies
- 2200/0086 . . relating to the Q factor or damping of the resonant circuit
- 2200/0088 . . Reduction of noise
- 2200/009 . . . Reduction of phase noise
- 2200/0092 . . Measures to linearise or reduce distortion of oscillator characteristics
- 2200/0094 . . Measures to ensure starting of oscillations
- 2200/0096 . . Measures to ensure stopping of oscillations
- 2200/0098 . . having a balanced output signal
- 2201/00 Aspects of oscillators relating to varying the frequency of the oscillations**
- 2201/01 . Varying the frequency of the oscillations by manual means
- 2201/011 . . the means being an element with a variable capacitance
- 2201/012 . . the means being an element with a variable inductance
- 2201/014 . . the means being associated with an element comprising distributed inductances and capacitances
- 2201/015 . . . the element being a cavity
- 2201/017 . . . the element being a dielectric resonator
- 2201/018 . . the means being a manual switch
- 2201/02 . Varying the frequency of the oscillations by electronic means
- 2201/0208 . . the means being an element with a variable capacitance, e.g. capacitance diode
- 2201/0216 . . the means being an element with a variable inductance
- 2201/0225 . . the means being associated with an element comprising distributed inductances and capacitances
- 2201/0233 . . . the element being a cavity
- 2201/0241 . . . the element being a magnetically variable element, e.g. an Yttrium Iron Garnet
- 2201/025 . . the means being an electronic switch for switching in or out oscillator elements
- 2201/0258 . . . the means comprising a diode
- 2201/0266 . . . the means comprising a transistor
- 2201/0275 . . the means delivering several selected voltages or currents
- 2201/0283 . . . the means functioning digitally
- 2201/0291 and being controlled by a processing device, e.g. a microprocessor
- 2201/03 . Varying beside the frequency also another parameter of the oscillator in dependence on the frequency
- 2201/031 . . the parameter being the amplitude of a signal, e.g. maintaining a constant output amplitude over the frequency range
- 2201/033 . . the parameter being the amount of feedback
- 2201/035 . . the parameter being another frequency, e.g. a harmonic of the oscillating frequency
- 2201/036 . . the parameter being the quality factor of a resonator
- 2201/038 . . the parameter being a bias voltage or a power supply
- 2202/00 Aspects of oscillators relating to reduction of undesired oscillations**
- 2202/01 . Reduction of undesired oscillations originated from distortion in one of the circuit elements of the oscillator
- 2202/012 . . the circuit element being the active device
- 2202/015 . . the circuit element being a limiter
- 2202/017 . . the circuit element being a frequency determining element
- 2202/02 . Reduction of undesired oscillations originated from natural noise of the circuit elements of the oscillator
- 2202/022 . . the noise being essentially white noise, i.e. frequency independent noise
- 2202/025 . . the noise being coloured noise, i.e. frequency dependent noise
- 2202/027 . . . the noise being essentially proportional to the inverse of the frequency, i.e. the so-called 1/f noise
- 2202/03 . Reduction of undesired oscillations originated from internal parasitic couplings, i.e. parasitic couplings within the oscillator itself
- 2202/04 . Reduction of undesired oscillations originated from outside noise or interferences, e.g. from parasitic couplings with circuit elements outside the oscillator
- 2202/042 . . the circuit element belonging to the power supply
- 2202/044 . . the circuit element belonging to transmitter circuitry
- 2202/046 . . the circuit element belonging to receiver circuitry
- 2202/048 . . the circuit element being a frequency divider
- 2202/05 . Reduction of undesired oscillations through filtering or through special resonator characteristics
- 2202/06 . Reduction of undesired oscillations through modification of a bias voltage, e.g. selecting the operation point of an active device
- 2202/07 . Reduction of undesired oscillations through a cancelling of the undesired oscillation
- 2202/073 . . by modifying the internal feedback of the oscillator

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- 2202/076 . . by using a feedback loop external to the oscillator, e.g. the so-called noise degeneration
- 2202/08 . Reduction of undesired oscillations originated from the oscillator in circuit elements external to the oscillator by means associated with the oscillator
- 2202/082 . . by avoiding coupling between these circuit elements
- 2202/084 . . . through shielding
- 2202/086 . . . through a frequency dependent coupling, e.g. which attenuates a certain frequency range
- 2202/088 . . by compensating through additional couplings with these circuit elements